2SC3004

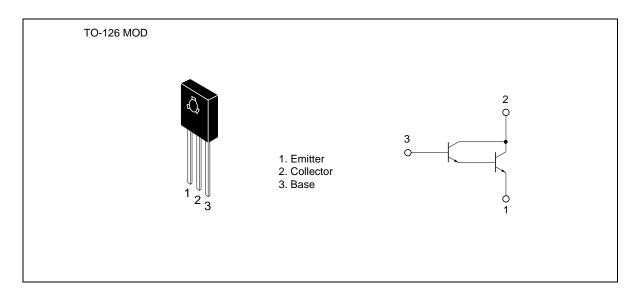
Silicon NPN Epitaxial

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Application

High gain amplifier medium speed switching

Outline



2SC3004

Absolute Maximum Ratings $(Ta = 25^{\circ}C)$

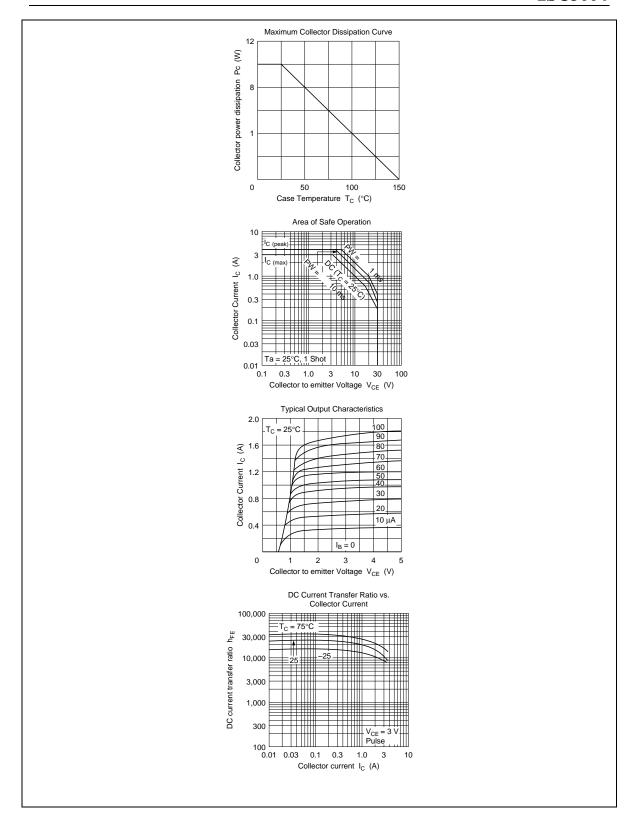
Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	30	V
Collector to emitter voltage	V _{CEO}	30	V
Emitter to base voltage	V _{EBO}	7	V
Collector current	I _c	3	A
Collector peak current	C(peak)	4	A
Collector power dissipation	P _c *1	10	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. Value at $T_c = 25$ °C.

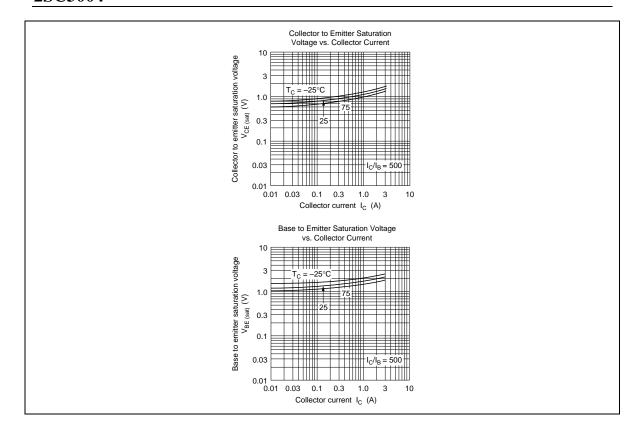
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	_	_	V	$I_{c} = 0.1 \text{ mA}, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	_	_	V	$I_c = 1 \text{ mA}, R_{BE} = _$
Emitter to base breakdown voltage	$V_{\text{(BR)EBO}}$	7	_	_	V	$I_{\rm E} = 0.1 \text{mA}, I_{\rm C} = 0$
Collector cutoff current	I _{CEO}	_	_	20	μΑ	V _{CE} = 24 V, R _{BE} = _
DC current transfer ratio	h _{FE}	2000	_	50000		$V_{CE} = 3 \text{ V}, I_{C} = 1.5 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1.5	V	$I_{\rm c} = 1.5 \text{ A}, I_{\rm B} = 3 \text{ mA*}^{1}$
		_	_	2.0	V	$I_{\rm C} = 3 \text{ A}, I_{\rm B} = 30 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$	_	_	2.0	V	$I_{c} = 1.5 \text{ A}, I_{B} = 3 \text{ mA*}^{1}$
		_	_	3.5	V	$I_{\rm C} = 3 \text{ A}, I_{\rm B} = 30 \text{ mA}^{*1}$
Turn on time	t _{on}	_	0.4	_	μs	$I_{c} = 1.5 \text{ A}, I_{B1} = -I_{B2} = 3 \text{ mA}$ $V_{cc} = 30 \text{ V}$
Turn off time	t _{off}	_	1.2		μs	_
Storage time	t _{stg}		0.8		μs	_

Note: 1. Pulse test



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